GTM CORPORATION

ISSUED DATE :2003/12/15
REVISED DATE :2004/11/29B

GPN2907A PNP EPITAXIAL PLANAR TRANSISTOR

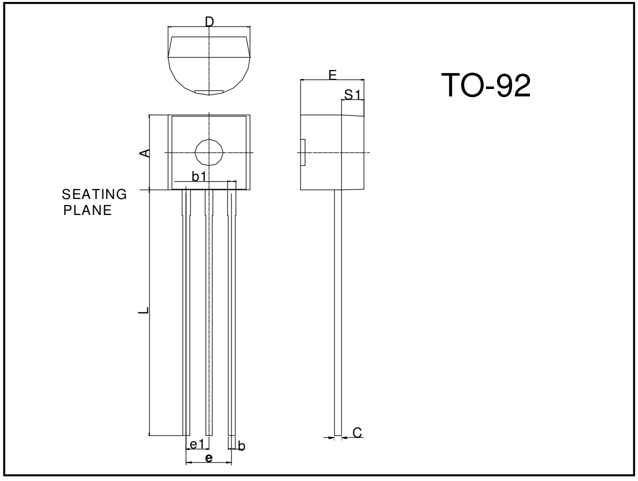
Description

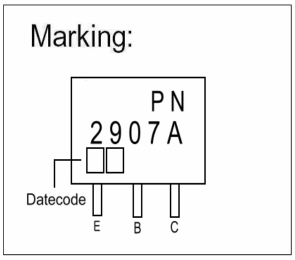
The GPN2907A is designed for general purpose amplifier and high speed, medium-power switching applications

Features

*Low Collect Saturation voltage.
*High Speed Switching.
*For Complementary Use with NPN Type GPN2222A.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	625	mW

Electrical Characteristics at Ta = 25℃

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-60	-	-	V	IC=-10uA, IE=0
BVCEO	-60	-	-	V	IC=-10mA, IB=0
BVEBO	-5	-	-	V	IC=-10uA, IC=0
ICBO	-	-	-10	nA	VCB=-50V, IC=0
ICEX	-	-	-50	nA	VCE-30V, VBE=-0.5
VCE(sat)1	-	-0.2	-0.4	V	IC=-150mA, IB=-15mA
VCE(sat)2	-	-0.5	-1.6	V	IC=-500mA, IB=-50mA
VBE(sat)1	-	-	-1.3	V	IC=-150mA, IB=-15mA
VBE(sat)2	-	-	-2.6	V	IC=-500mA, IB=-50mA
hFE1	75	-	-		VCE=-10V, IC=-100uA
hFE2	100	-	-		VCE=-10V, IC=-1mA
hFE3	100				VCE=-10V, IC=-10mA
hFE4	100	180	300		VCE=-10V, IC=-150mA
hFE5	50	-	-		VCE=-10V, IC=-500mA
fT	200	-	-	MHZ	VCE=-20V,IC=-50mA,f=100MHZ
Cob	-	-	8	pF	VCB=-10V,F=1MHZ

Characteristics Curve